Analog Power AM4407PE

P-Channel 30-V (D-S) MOSFET

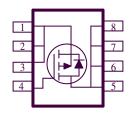
These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY			
$V_{DS}(V)$	$r_{DS(on)} m(\Omega)$	$I_{D}(A)$	
-30	9 @ $V_{GS} = -10V$	-15	
	13 @ $V_{GS} = -4.5V$	-11	

- Low r_{DS(on)} provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOIC-8 saves board space
- Fast switching speed
- High performance trench technology







Protected

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Maximum	Units	
Drain-Source Voltage			-30	V	
Gate-Source Voltage			±20		
Caratina and Davis Carana a	T _A =25°C	Τ_	-15		
Continuous Drain Current ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	ъ	-11	A	
Pulsed Drain Current ^b			±50		
Continuous Source Current (Diode Conduction) ^a		I_S	-2.1	A	
D a	$T_A=25^{\circ}C$	D	3.1	\mathbf{w}	
Power Dissipation ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	rD	2.3	**	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Case ^a	t <= 5 sec	$R_{ heta JC}$	25	°C/W	
Maximum Junction-to-Ambient ^a	t <= 5 sec	$R_{ heta JA}$	50	°C/W	

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

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SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Cl1	T 4 C 122	Limits			TI	
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1			V	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±10	μΑ	
Zero Gate Voltage Drain Current	ī	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ	
Zero Gate Voltage Brain Current	I_{DSS}	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-5		
On-State Drain Current ^A	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-50			A	
Drain-Source On-Resistance ^A	r _{DS(on)}	$V_{GS} = -10 \text{ V}, I_{D} = -1 \text{ A}$			9	mΩ	
Drain-Source On-Resistance		$V_{GS} = -4.5 \text{ V}, I_{D} = -1 \text{ A}$			13		
Forward Tranconductance ^A	$g_{ m fs}$	$V_{DS} = -5 \text{ V}, I_{D} = -1 \text{ A}$		44		S	
Diode Forward Voltage	V_{SD}	$I_{S} = 1 \text{ A}, V_{GS} = 0 \text{ V}$		-0.7		V	
Dynamic ^b					•	•	
Total Gate Charge	Q_{g}	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V},$		50			
Gate-Source Charge	Q_{gs}	$I_D = -1 A$		10		nC	
Gate-Drain Charge	Q_{gd}	ID = 171		20			
Switching							
Turn-On Delay Time	$t_{d(on)}$			10			
Rise Time	t _r	$V_{DD} = -15 \text{ V}, R_L = 6 \Omega, ID = -1 \text{ A},$		30		nS	
Turn-Off Delay Time	$t_{\rm d(off)}$	VGEN = -10 V		100		113	
Fall-Time	t_{f}			50			

Notes

a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.

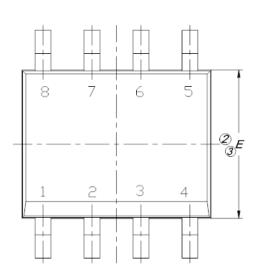
b. Guaranteed by design, not subject to production testing.

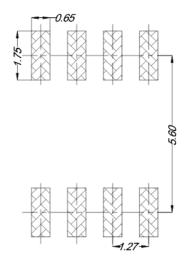
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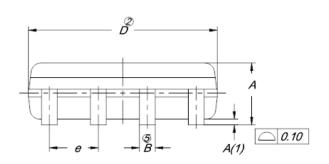
Package Information

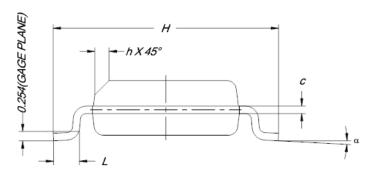
Land Pattern (Only for Reference)





DIM.	MILLIMETERS			
	MIN.	NOM.	MAX.	
Α	1.35	1.55	1.75	
A(1)	0.10	0.18	0.25	
В	0.38	0.45	0.51	
С	0.19	0.22	0.25	
D	4.80	4.90	5.00	
Е	3.80	3.90	4.00	
е	1.27 BSC			
Н	5.80	6.00	6.20	
L	0.50	0.72	0.93	
α	0°	4°	8°	
h	0.25	0.38	0.50	





Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- 4. The Package Top May Be Smaller Than The Package Bottom.
- 5. Dimension "B" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.08 mm Total In Excess Of "B" Dimension At Maximum Material Condition. The Dambar Cannot Be Located On The Lower Radius Of The Foot.